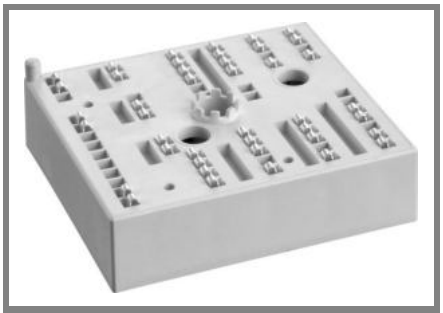
SKiiP 28AHB16V3



MiniSKiiP® 2

3-phase bridge rectifier + brake chopper

SKiiP 28AHB16V3

Target Data

Features

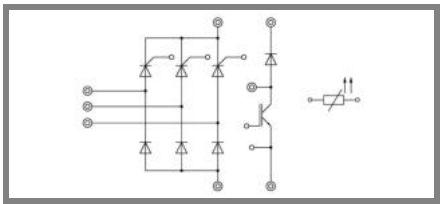
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

- V_{CEsat} , V_F = chip level value

Absolute Maximum Ratings		T_s = 25 °C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT - Chopper			
V_{CES}		1200	V
I_C	T_s = 25 (70) °C	118 (88)	A
I_{CRM}	$t_p \leq$ 1 ms	210	A
V_{GES}		± 20	V
T_j		-40...+150	°C
Diode - Chopper			
I_F	T_s = 25 (70) °C	118 (88)	A
I_{FRM}	$t_p \leq$ 1 ms	210	A
T_j		-40...+150	°C
Diode / Thyristor - Rectifier			
V_{RRM}		1600	V
I_F / I_T	T_s = 70	82	A
I_{FSM} / I_{TSM}	t_p = 10 ms, sin 180 °, T_j = 25 °C	1000	A
i^2t	t_p = 10 ms, sin 180 °, T_j = 25 °C	5500	A^2s
T_j	Diode	-40...+150	°C
T_j	Thyristor	-40...+125	°C
I_{tRMS}	per power terminal (20 A / spring)	80	A
T_{stg}	$T_{op} \leq T_{stg}$	-40...+125	°C
V_{isol}	AC, 1 min.	2500	V

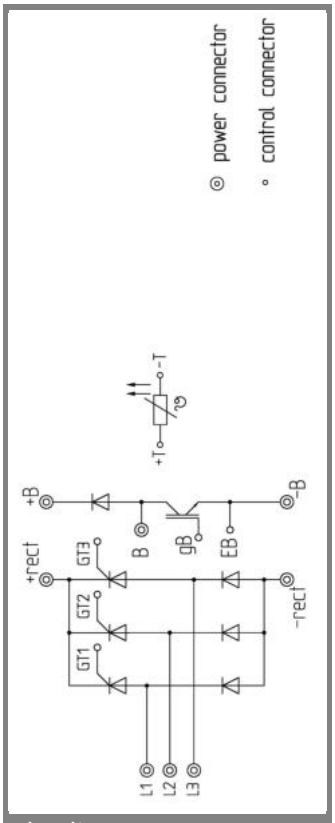
Characteristics		T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT - Chopper					
V_{CEsat}	I_{Cnom} = 105 A, T_j = 25 (125) °C		1,7 (2)	2,1 (2,4)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, I_C = 3 mA	5	5,8	6,5	V
$V_{CE(TO)}$	T_j = 25 (125) °C		1 (0,9)	1,2 (0,9)	V
r_T	T_j = 25 (125) °C		6,7 (10)	8,6 (10)	mΩ
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		8,4		nF
C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1,5		nF
C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1,1		nF
$R_{th(j-s)}$	per IGBT		0,4		K/W
$t_{d(on)}$	under following conditions		65		ns
t_r	V_{CC} = 600 V, V_{GE} = ± 15 V		30		ns
$t_{d(off)}$	I_{Cnom} = 105 A, T_j = 125 °C		410		ns
t_f	$R_{Gon} = R_{Goff}$ = 5,5 Ω		100		ns
E_{on}	inductive load		14,4		mJ
E_{off}			13,3		mJ
Diode - Chopper					
$V_F = V_{EC}$	I_{Fnom} = 105 A, T_j = 25 (125) °C		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	T_j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r_T	T_j = 25 (125) °C		5,7 (7,6)	6,7 (8,6)	mΩ
$R_{th(j-s)}$	per diode		0,55		K/W
I_{RRM}	under following conditions		160		A
Q_{rr}	I_{Fnom} = 105 A, V_R = 600 V		26		µC
E_{rr}	V_{GE} = 0 V, T_j = 125 °C		10,8		mJ
	di_F/dt = 5400 A/µs				



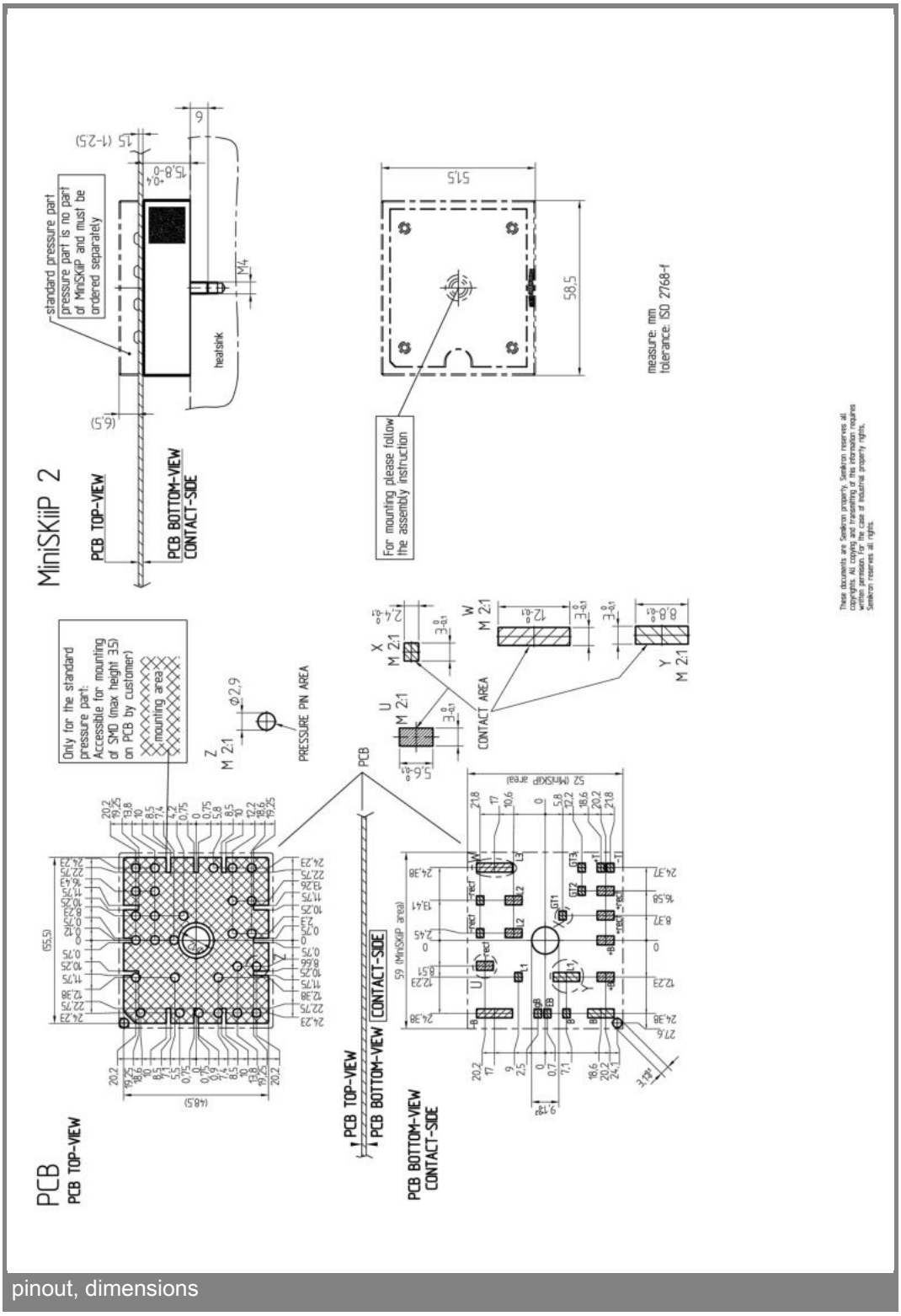
AHB

Characteristics		T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
Diode - Rectifier					
V_F	I_{Fnom} = 75 A, T_j = 25 °C		1,2		V
$V_{(TO)}$	T_j = 150 °C		0,8		V
r_T	T_j = 150 °C		7		mΩ
$R_{th(j-s)}$	per diode		0,7		K/W
Thyristor - Rectifier					
V_T	I_{Fnom} = 120 A, T_j = 25 (125) °C			1,8 (1,7)	V
$V_{T(TO)}$	T_j = 125 °C			1,1	V
r_T	T_j = 125 °C			5	mΩ
V_{GT}	T_j = 25 °C			3	V
I_{GT}	T_j = 25 °C	150			mA
I_H	T_j = 25 °C		200		mA
I_L	T_j = 25 °C		400		mA
$dv/dt_{(cr)}$	T_j = 125 °C			1000	V/µs
$di/dt_{(cr)}$	T_j = 125 °C			50	A/µs
$R_{th(j-s)}$	per thyristor		0,65		K/W
Temperature Sensor					
R_{ts}	3 %, T_r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			65		g
M_s	Mounting torque	2		2,5	Nm

SKiiP 28AHB16V3



circuit



pinout, dimensions

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

